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(54) Title: DOPANT CONCENTRATION CONTROL IN SILICON MELT TO ENHANCE THE INGOT QUALITY

(57) Abstract: Methods for producing single crystal silicon ingots in which the dopant concentration in the silicon melt is controlled are disclosed. The control of the dopant concentration enhances ingot quality by the reduction or elimination of dislocations in the neck, crown, and main body portions of the single crystal silicon ingot.

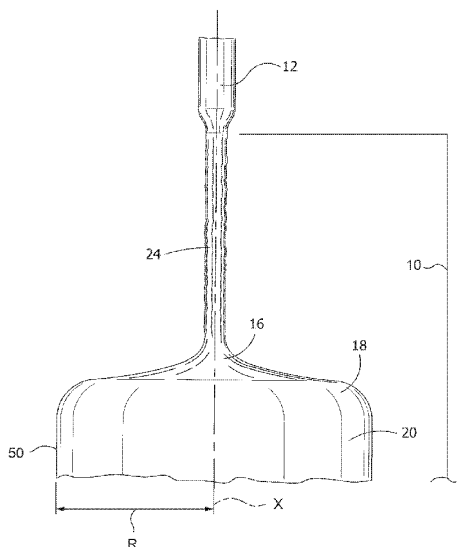


FIG. 1

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